

Supplementary

Electrical, Structural, Optical and Adhesive Characteristics of Aluminum-Doped Tin Oxide Thin Films for Transparent Flexible Thin-Film Transistor Applications

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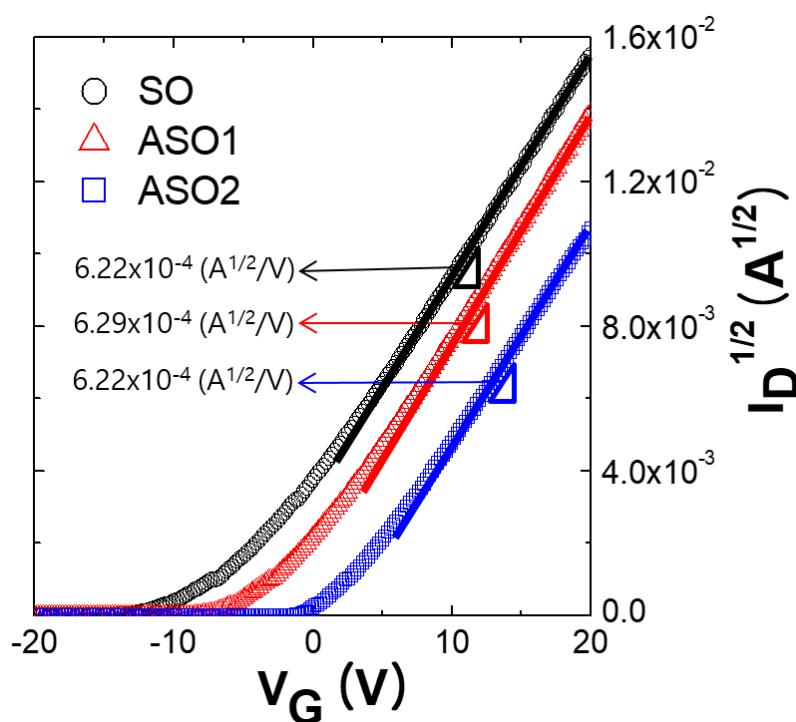


Figure S1. The $(I_D)^{1/2}$ versus V_G curves of SO, ASO1, and ASO2 TFTs for comparison of electron mobilities at $V_D = 10.1V$.